



DMT6012LSS

#### **Product Summary**

BV <sub>DSS</sub>	Rds(on) Max	I <sub>D</sub> Max Ta = +25°C
c0)/	11mΩ @ V <sub>GS</sub> = 10V	10.4A
60V	14mΩ @ V <sub>GS</sub> = 4.5V	9.3A

## **Description and Applications**

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- High Frequency Switching
- Synchronous Rectification
- DC-DC Converters

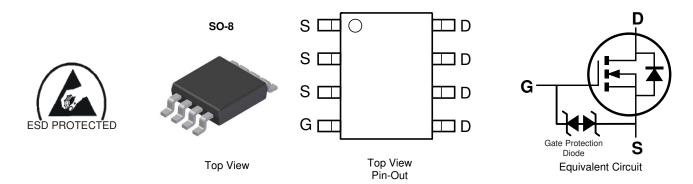
#### 60V N-CHANNEL ENHANCEMENT MODE MOSFET

### **Features and Benefits**

- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low RDS(ON) Minimizes On-State Losses
- Low Input Capacitance
- Fast Switching Speed
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. <u>https://www.diodes.com/quality/product-definitions/</u>

### **Mechanical Data**

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound.
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 🚱
- Weight: 0.074 grams (Approximate)



#### Ordering Information (Note 4)

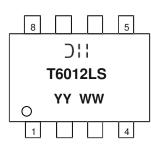
Part Number	Case	Packaging
DMT6012LSS-13	SO-8	2,500/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and

Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**



 $C_{++} = Manufacturer's Marking T6012LS = Product Type Marking Code YYWW = Date Code Marking YY or <math>\overline{YY} = Year (ex: 20 = 2020)$  WW = Week (01 to 53)

DMT6012LSS Document number: DS40135 Rev. 3 - 2



# Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	60	V
Gate-Source Voltage			VGSS	±20	V
Continuous Drain Current (Note 6) $V_{GS}$ = 10V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	ID	10.4 8.4	A
Maximum Continuous Body Diode Forward Current (Note 6)			ls	10	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	65	А
Avalanche Current, L = 0.3mH			las	15.8	А
Avalanche Energy, L = 0.3mH			Eas	37.5	mJ

### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	TA = +25°C	PD	1.2	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	RθJA	106	°C/W
Total Power Dissipation (Note 6)	TA = +25°C	PD	1.84	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R <sub>0JA</sub>	68	°C/W
Thermal Resistance, Junction to Case (Note 6)		Rejc	9.2	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

### Electrical Characteristics (T<sub>A</sub> = +25°C, unless otherwise specified.)

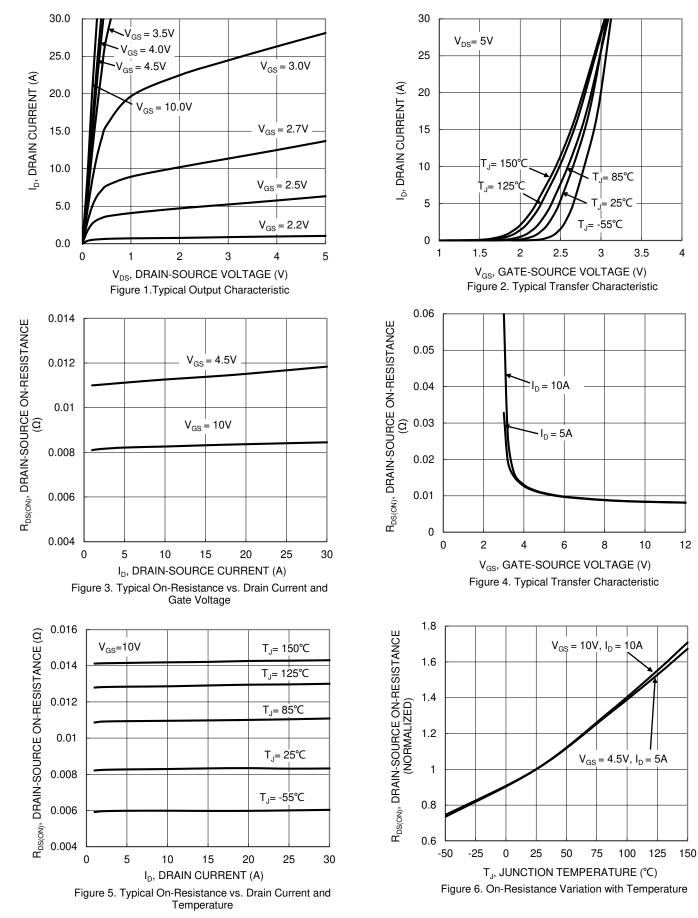
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)	· ·					
Drain-Source Breakdown Voltage	BVDSS	60	—	—	V	$V_{GS} = 0V, I_D = 1mA$
Zero Gate Voltage Drain Current	IDSS		—	1	μA	$V_{DS} = 48V, V_{GS} = 0V$
Gate-Source Leakage	lgss		—	±10	μA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)			-			
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.7	—	2	V	$V_{DS}=V_{GS},\ I_{D}=250\mu A$
Static Drain-Source On-Resistance	Descent	_	8.4	11		$V_{GS} = 10V, I_D = 10A$
Static Drain-Source On-Resistance	RDS(ON)		11.5	14	mΩ	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 5A
Diode Forward Voltage	Vsd		0.8	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 20A
DYNAMIC CHARACTERISTICS (Note 8)						-
Input Capacitance	Ciss	_	1522	_		$V_{DS} = 30V, V_{GS} = 0V,$ f = 1MHz
Output Capacitance	Coss		352	—	pF	
Reverse Transfer Capacitance	Crss		27.5	—		
Gate Resistance	Rg		1.4	—	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg		10.7	_		
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg		22.2	—	nC	Vps = 30V. lp = 10A
Gate-Source Charge	Qgs		3.3	—	no	VDS = 30V, ID = 10A
Gate-Drain Charge	Q <sub>gd</sub>		4.2	_		
Turn-On Delay Time	t <sub>D(ON)</sub>	_	4.4	_		
Turn-On Rise Time	tR	—	6.7	—		$\label{eq:VGS} \begin{array}{l} V_{GS} = 10V,  V_{DS} = 30V, \\ R_G = 6\Omega,  I_D = 10A \end{array}$
Turn-Off Delay Time	td(OFF)	_	25.5	—	ns	
Turn-Off Fall Time	tF		12.5		]	
Body Diode Reverse Recovery Time	trr	_	25.8	—	ns	
Body Diode Reverse Recovery Charge	Qrr		15.1	—	nC	$I_F = 10A$ , di/dt = 100A/µs

 Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate. Notes:

Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.

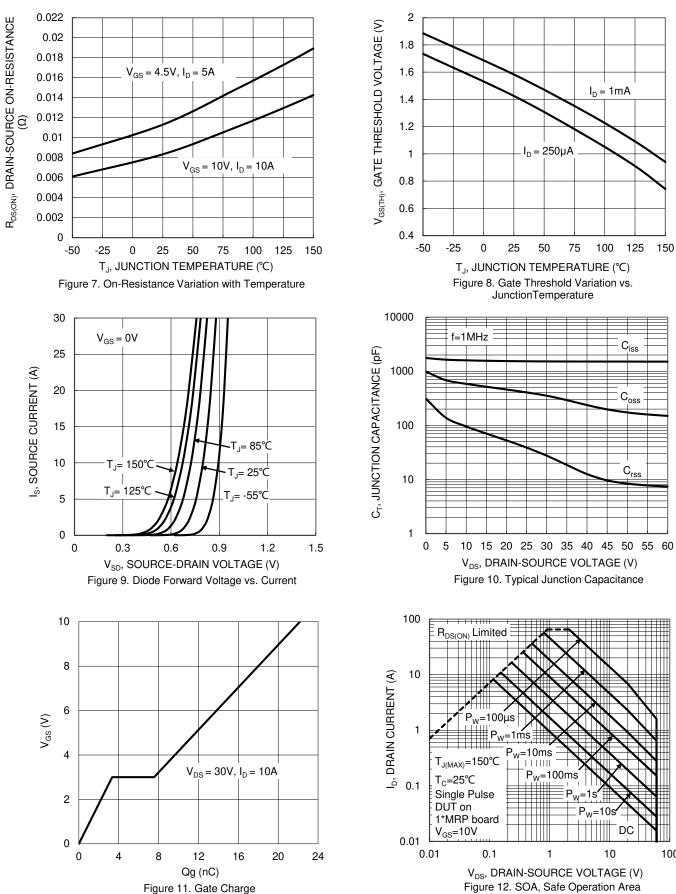


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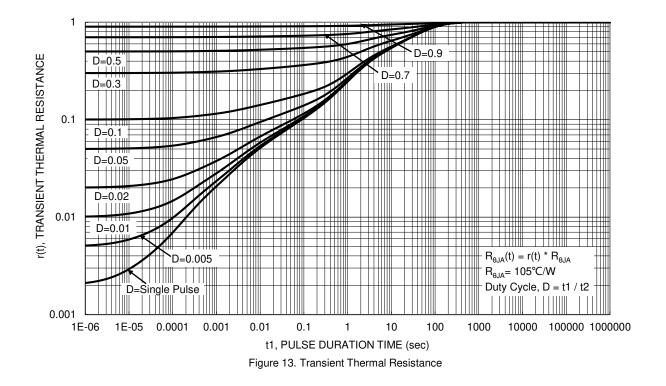


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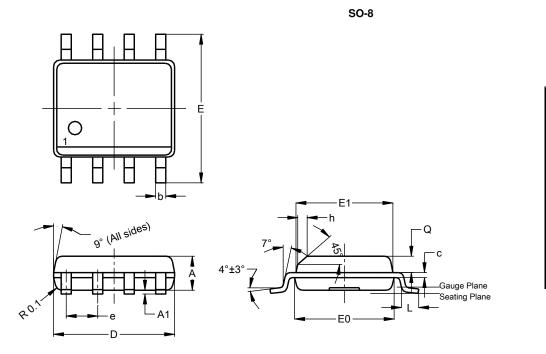






### **Package Outline Dimensions**

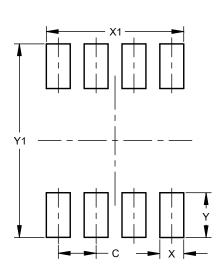
Please see http://www.diodes.com/package-outlines.html for the latest version.



SO-8					
Dim	Min	Max	Тур		
Α	1.40	1.50	1.45		
A1	0.10	0.20	0.15		
b	0.30	0.50	0.40		
C	0.15	0.25	0.20		
D	4.85	4.95	4.90		
Е	5.90	6.10	6.00		
E1	3.80	3.90	3.85		
E0	3.85	3.95	3.90		
е	<b>e</b> 1.27				
h			0.35		
L	0.62	0.82	0.72		
Q	0.60	0.70	0.65		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



SO-8

Dimensions	Value (in mm)			
С	1.27			
Х	0.802			
X1	4.612			
Y	1.505			
Y1	6.50			



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